



矽普

Siliup Semiconductor

SP010N110GP8

100V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}TYP$	I_D
100V	110m Ω @10V	5A

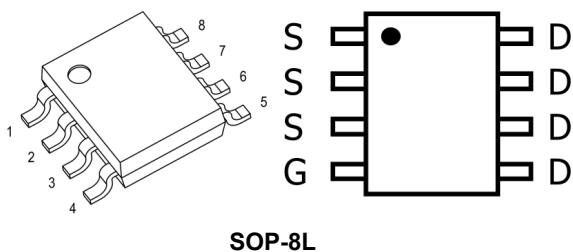
Feature

- VDS 100V
- ID 5.0A
- $R_{DS(ON)}$ (at $VGS=10V$) < 140 mohm

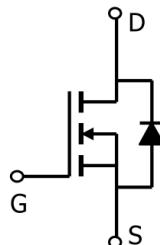
Applications

- Consumer electronic power supply
- Motor control
- Synchronous-rectification
- Isolated DC/DC convertor
- Invertors

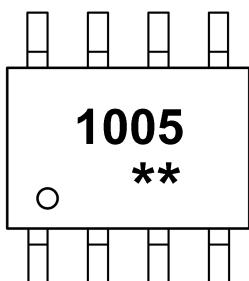
Package



Circuit diagram



Marking



1005 : Product code
** : Week code.



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Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current – Continuous	I _D	5	A
Drain Current – Pulsed ¹	I _{DM}	20	A
Power Dissipation (TC=25°C)	P _D	1.9	W
Thermal Resistance Junction to ambient	R _{θJA}	65.8	°C/W
Storage Temperature Range	T _{STG}	-50 to 150	°C
Operating Junction Temperature Range	T _J	-50 to 150	°C

Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	B _{VDSS}	V _{GS} =0V , ID=250uA	100	---	---	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =100V , V _{GS} =0V	---	---	1	uA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , ID = 250uA	1	1.8	3	V
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V , V _{DS} =0V	---	---	100	nA
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V , ID=3A	---	110	140	mΩ
		V _{GS} =4.5V , ID=2A	---	160	300	mΩ
Dynamic Characteristics						
Total Gate Charge	Q _g	V _{GS} =10V,V _{DS} =50V, ID=3.0A	---	4.3	---	nC
Gate-Source Charge	Q _{gs}		---	1.5	---	
Gate-Drain Charge	Q _{gd}		---	1.1	---	
Turn-On Delay Time	T _{d(on)}	V _{GS} =10V,V _{DD} =50V, ID=3.0A, R _{GEN} =2Ω	---	14.7	---	ns
Rise Time	T _r		---	3.5	---	
Turn-Off Delay Time	T _{d(off)}		---	20.9	---	
Fall Time	T _f		---	2.7	---	
Input Capacitance	C _{iss}	V _{DS} =50V,V _{GS} =0V,f=1MHZ	---	206	---	pF
Output Capacitance	C _{oss}		---	29	---	
Reverse Transfer Capacitance	C _{rss}		---	1.4	---	
Drain-Source Body Diode Characteristics						
Continuous Source Current	I _s	VG=VD=0V , Force Current	---	---	5	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V , IS=3A , TJ=25°C	---	---	1.2	V



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Typical Characteristics

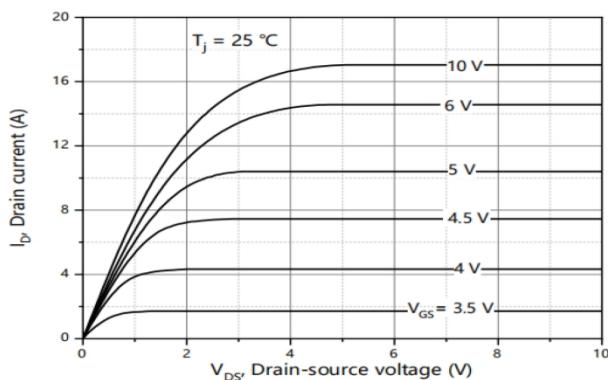


Figure1. Output Characteristics

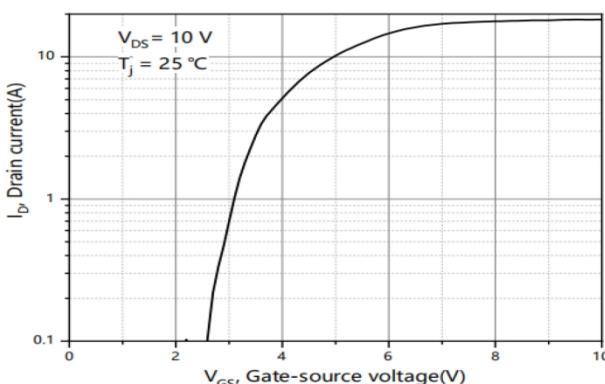


Figure2. Transfer Characteristics

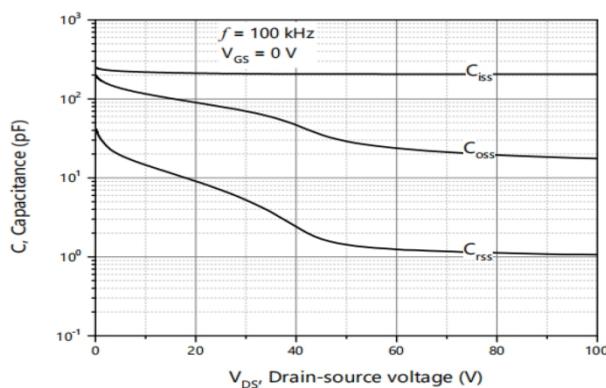


Figure3. Capacitance Characteristics

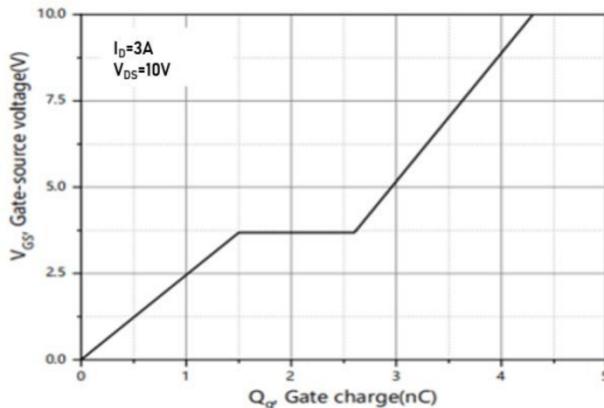


Figure4. Gate Charge

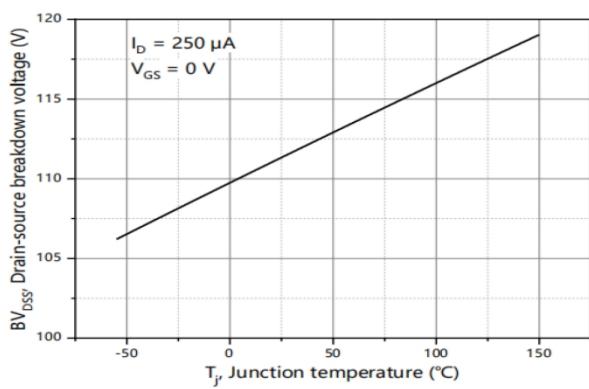


Figure5. Drain-Source breakdown voltage

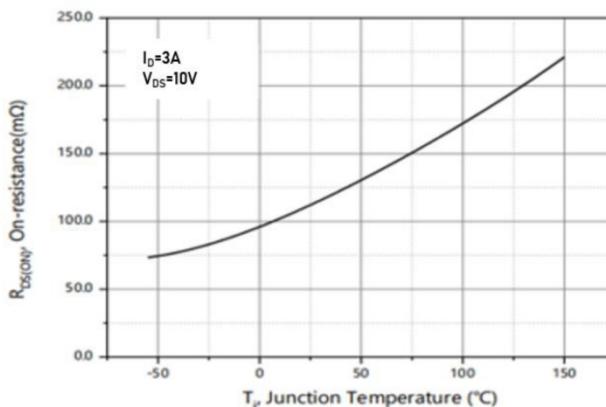


Figure6. Drain-Source on Resistance

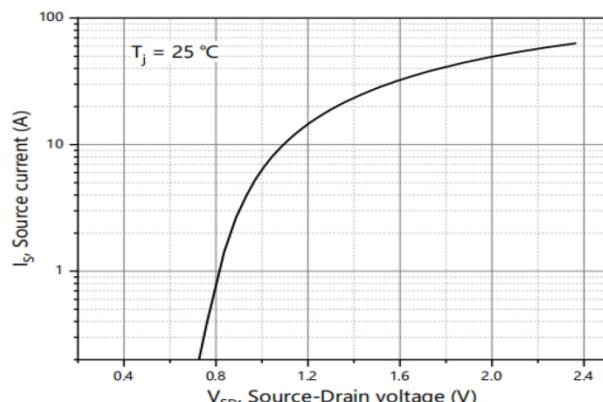


Figure7. Forward characteristic of body diode

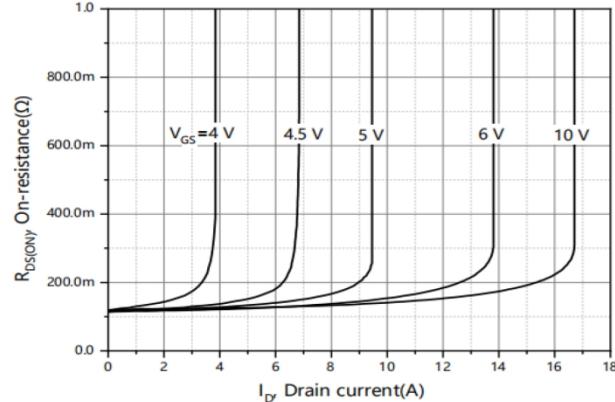


Figure8. Drain-source on-state resistance



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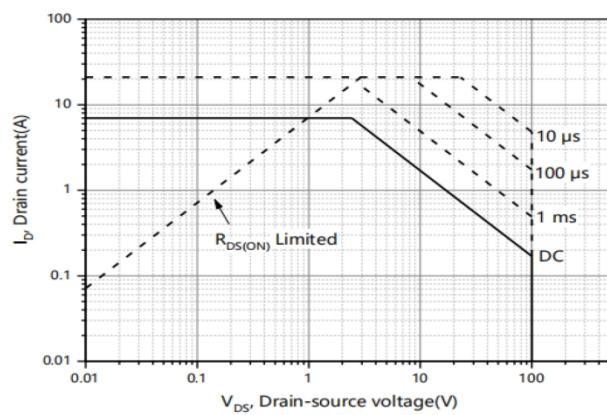


Figure9. Safe Operation Area $T_A=25\text{ }^{\circ}\text{C}$

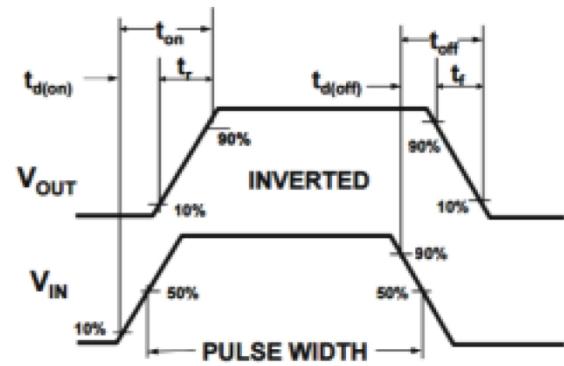


Figure10. Switching wave



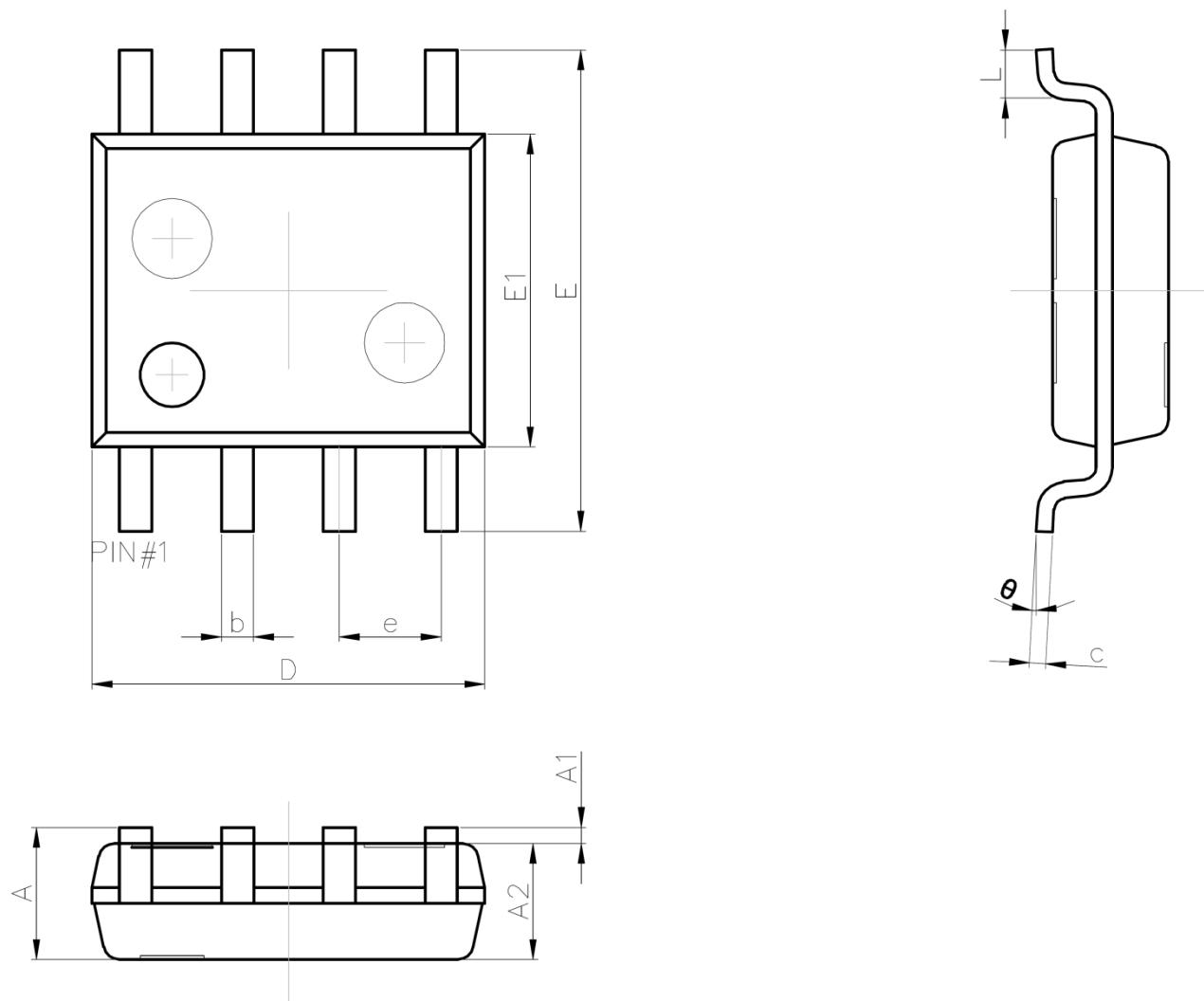
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SOP-8 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°